



浙江芯芯电子有限公司
ZHEJIANG XINXIN ELECTIRICAL CO., LTD.

产品规格书

Specification of Products

产品名称：平板型晶闸管

产品型号：KP400A

浙江芯芯电子有限公司

ZHEJIANG XINXIN ELECTIRICAL CO., LTD.

地址：浙江省缙云县壶镇镇浙江丽缙五金科技产业园苍山区块内

电话：13857067071

邮编：321404

E-mail:247145749@qq.com

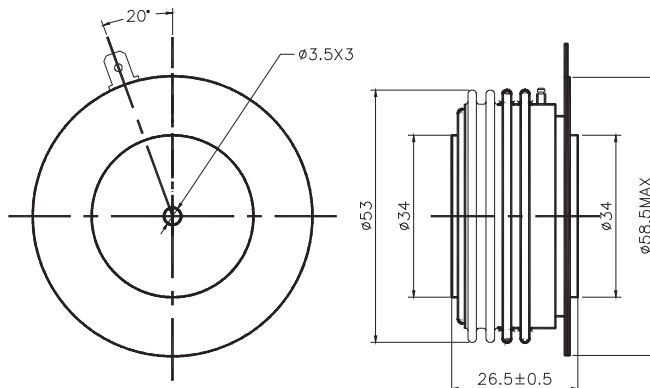
<http://www.zjxxdz1.com>

拟制	审核	核准
丁国盛	李园利	麻伟阳

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SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (C)	VALUE			UNIT
				Min	Type	Max	
I _{T(AV)}	Mean on-state current	180 half sinewave 50Hz Double side cooled, T _{ns} =55 C	125			855	A
I _{T(AV)}	Mean on-state current	180 half sinewave 50Hz Double side cooled, T _{ns} =80 C	125			646	A
V _{DRM} V _{RRM}	Repetitive peak on-state voltage Repetitive peak reverse voltage	V _{DRM} &V _{RRM} tp=10ms V _{Dsm} &V _{Rsm} = V _{DRM} &V _{RRM} +100V respectively	125	800		1800	V
I _{DRM} I _{RRM}	Repetitive peak current	at V _{DRM} at V _{RRM}	125			40	mA
I _{TSM}	Surge on-state current	10ms half sinewave	125			9.2	KA
I ² T I	² T for fusing coordination	V _R =0.6V _{RRM}				423 A ² s*10 ³	
V _{TO}	Threshold voltage		125			0.91	V
r _T	On-state slop resistance					0.68	mΩ
V _{TM}	Peak on-state voltage	T _M =1700A, F=15KN	125			2.07	V
dv/dt	Critical rate of rise of off-state voltage	V _{DM} =0.67V _{DRM}	125			300	V/μs
di/dt	Critical rate of rise of on-state current	From 67%V _{DRM} to 1000A, Gate source 1.5A t _r ≤ 0.5μs Repetitive	125			300	A/μs
I _{rm}	Reverse recovery current	I _{TM} =500A, tp=1000 s, di/dt=-20A/s, V _r =50V	125			140	A
t _{rr}	Reverse recovery time					15	s
Q _{rr}	Recovery charge					1050	C
I _{GT}	Gate trigger current	V _A =12 V, I _A =1A	25	35		250	mA
V _{GT}	Gate trigger voltage			0.8		2.5	V
I _H	Holding current			20		200	mA
V _{GD}	Non-trigger gate voltage	At 67%V _{DRM}	125			0.3	V
R _{th(j-h)}	Thermal resistance Junction to heatsink	At 180° sine double side cooled Clamping force 15KN				0.035	C /W
F _m	Mounting force			10		20	KN
T _{stg}	Stored temperature			-40		140	C
W _t	Weight				270		g
Outline	KT33cT						

Outline



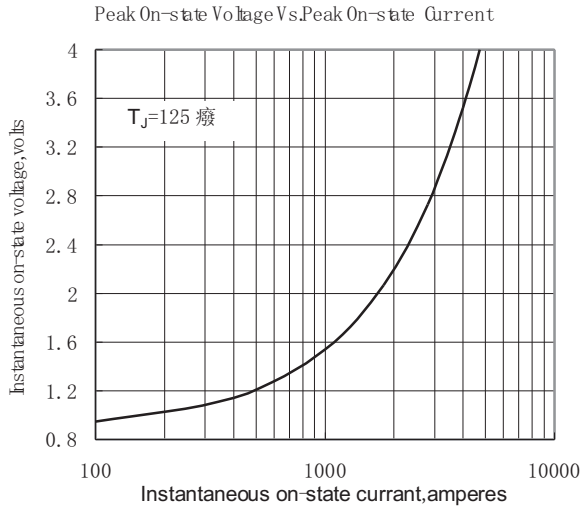


Fig. 1

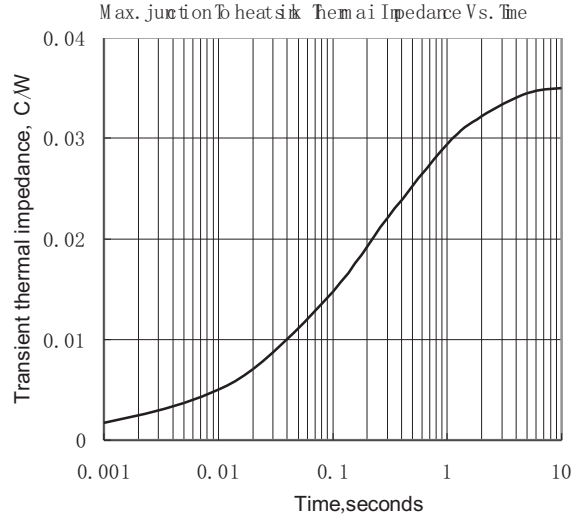


Fig. 2

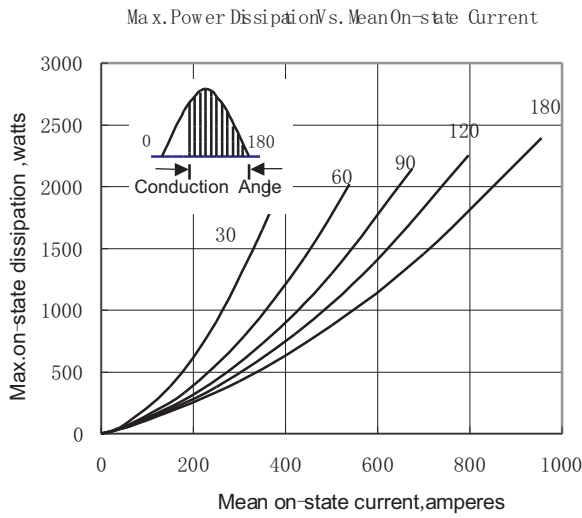


Fig. 3

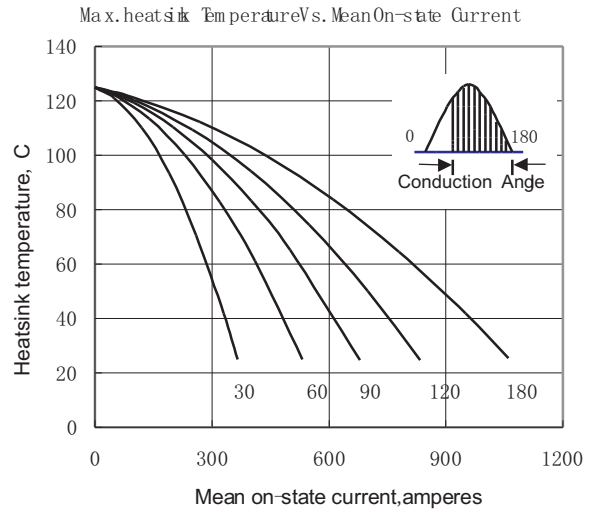


Fig. 4

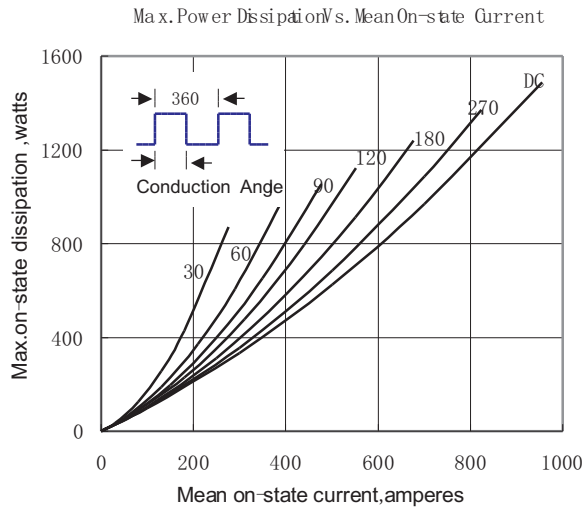


Fig. 5

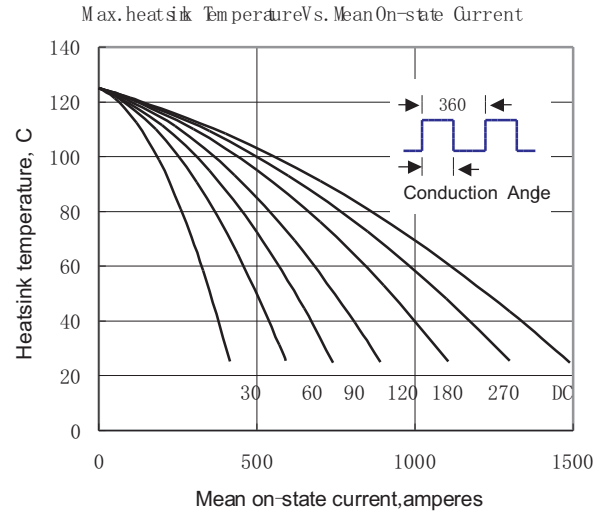


Fig. 6

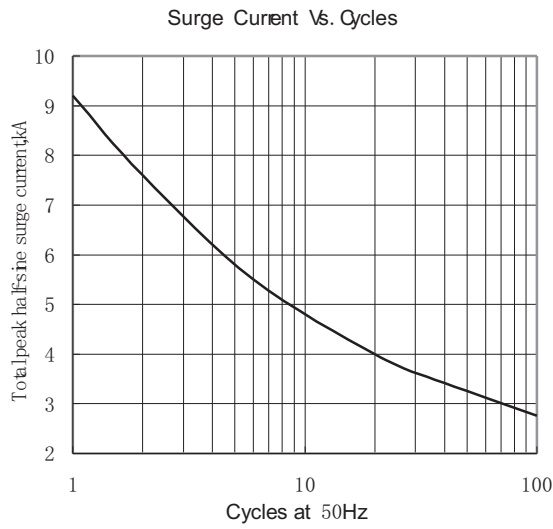


Fig. 7

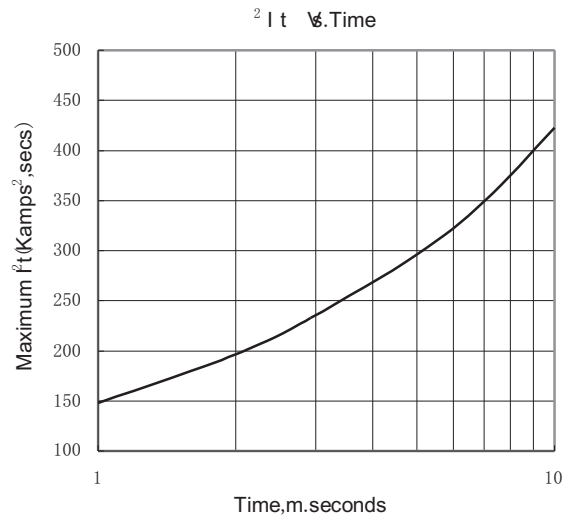


Fig. 8

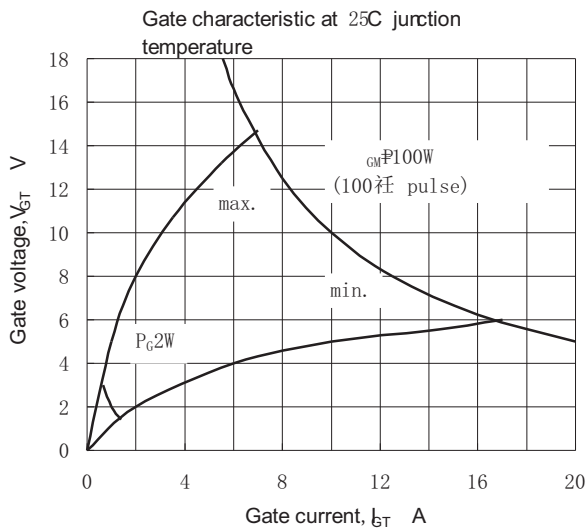


Fig. 9

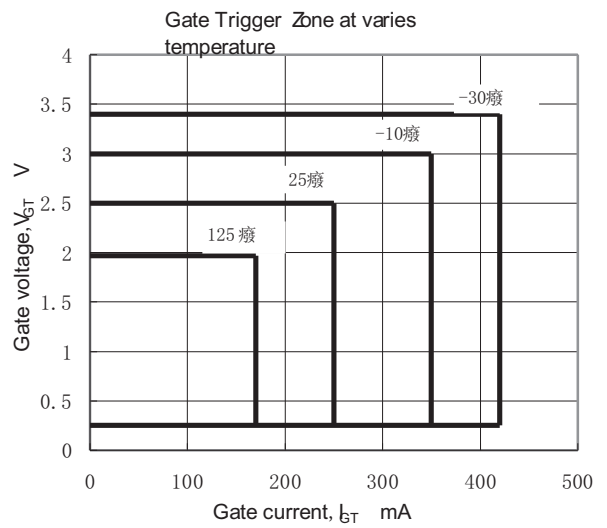


Fig. 10